

COMPOUND SEMICONDUCTOR WEEKEND

KAUST, Saudi Arabia September 2-5

Friday 02-09-2022 Day 1

Guest Arrival and Check in at KAUST Inn 2, Welcome Lunch, Golfing and Welcome Dinner

Saturday 03-09-2022 Day 2

Opening Ceremony, Sessions 1-4, Poster Competition, Banquet

Sunday 04-09-2022 Day 3

Sessions 5-6, Closing Ceremony, Lab Tour, Jeddah Tour and Dinner

Monday 05-09-2022 Day 4

Guest Departure

8:00-9:00	nda (Draft) urday 03-09-2022 Registration Location: RM5209, B3
8:00-9:00 Openin	Registration
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openii	ng Ceremony
Location: RM5209. F	33 Moderator: Xiaohang Li
9:00-9:05 Opening remarks by Prof. Tony C	
	Chaturvedi, Director of IIT Roorkee
	Shahid Alam, Consul General of India in Jeddah
	s by Dr. Daniel Acevedo-Feliz, Director, Core Labs and
Research Infrastructure, KAUST	, , ,
9:30-9:45	Group Photography
J	Location: Stairs near B16
	Session 1
Location: RM52	209, B3 Moderator: Dr. Md. Hasan Raza
9:45-10:15 Prof. Mario Lanza, KAUST	
Hexagonal Boron Nitride Based N	
10:15-10:45 Prof. Shaibal Mukherjee, IIT Indo	
Machine learning with crossbar m	
10:45-11:00 Saravanan Yuvaraja, Ph.D. studen	
Ultrawide bandgap Ga ₂ O ₃ -based O	
11:00-11:20	Bandgap break
	Session 2
	15209, B3 Moderator: Akash Jadhav
11:20-11:50 Prof. Yatin Wang, KAUST	
Recent advances of light sources in	
11:50-12:20 Prof. Sudharsanan Srinivasan, IIT	
Heterogeneous integration of III-V	
12:20-12:35 Dr. Md. Hasan Raza, Postdoctoral	
	volatile Charge Trapping Memory Devices and
Computing Applications 12:35-14:20 Lun	ch and Poster Competition
	rt Side, B3 Moderator: Prof. Biplab Sarkar
Location. L2 Desc	Session 3
Location	: RM5209, B3 Moderator: Yi Lu
14:30-15:00 Prof. Biplab Sarkar,IIT Roorkee	. Idvio 2007, Bo ivio defautor. 11 Bu
Ultra-wide bandgap Superjunction	n Power Devices
15:00-15:30 Prof. Ahmed K. Allehyani, Univer	
	ap Devices on Power Converters Design
15:30-15:45 Feras Algatari, Ph.D. student, KA	
	gh Boron Composition BGaN on AlN and GaN
15:45-16:05	Bandgap break
	Session 4
Location: RM	15209, B3 Moderator: Feras Algatari
	Khee Ng, and Prof. Boon S. Ooi, KAUST
Compound semiconductor optoele	

17:05-17:20 Akash Jadhav, Ph.D. student, IIT Roorkee An Approach to Develop Accurate Small Signal Model of AlGaN/GaN MOS-HEMTS 18:15-20:30 Banquet (Invitation only) Location: Pure Restaurant Day 3: Sunday 04-09-2022 Session 5 Location: RM5209, B3 Moderator: Mritunjay Kumar 9:00-9:30 Prof. Iman Roqan, KAUST The effect of carrier dynamics on optical efficiency in III-nitride devices: advanced opti analyses 9:30-10:00 Prof. Oves Badami, IIT Hyderabad Modelling and Simulations of III-V MOS transistors 10:00-10:15 Yi Lu, Ph.D. student, KAUST Advanced III-Oxide Semiconductor Membrane for Flexible/Vertical Electronics 10:15-10:35 Bandgap break Session 6 Location: RM5209, B3 Moderator: Saravanan Yuvaraja		Prof. Tanmoy Pramanik, IIT Roorkee Large-area Growth of Transition Metal Chalcogenides: Experiment and Modeling
18:15-20:30 Banquet (Invitation only) Location: Pure Restaurant Day 3: Sunday 04-09-2022 Session 5 Location: RM5209, B3 Moderator: Mritunjay Kumar 9:00-9:30 Prof. Iman Roqan, KAUST The effect of carrier dynamics on optical efficiency in III-nitride devices: advanced optical analyses 9:30-10:00 Prof. Oves Badami, IIT Hyderabad Modelling and Simulations of III-V MOS transistors 10:00-10:15 Yi Lu, Ph.D. student, KAUST Advanced III-Oxide Semiconductor Membrane for Flexible/Vertical Electronics 10:15-10:35 Bandgap break Session 6 Location: RM5209, B3 Moderator: Saravanan Yuvaraja	17:05-17:20	Akash Jadhav, Ph.D. student, IIT Roorkee
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L 10.25 11.05 L Drof Noral Eletah VALICT	10:35-11:05	Prof. Nazek Elatab, KAUST
Smart Memory Devices for the Digital Transformation	10:33-11:03	
11:05-11:35 Prof. Ankush Bag, IIT Guwahati	11:05-11:35	
Ga_2O_3 for emerging power and optoelectronics	11.05 11.55	
11:35-11:50 Chuanju Wang, Ph.D. student, KAUST	11:35-11:50	
Impact of the interfacial gate oxide morphology on the performance of GaN HEMTs		
Closing ceremony	11.50 12.05	Closing ceremony
Location: RM5209, B3 Moderator: Prof. Xiaohang Li & Prof. Biplab Sarkar	11:50-12:05	Location: RM5209, B3 Moderator: Prof. Xiaohang Li & Prof. Biplab Sarkar
Lunch break (Invitation-only)	12.15 12.50	Lunch break (Invitation-only)
Location: Reserved Tables of Campus Diner	12:15-15:50	Location: Reserved Tables of Campus Diner
14:00-17:00 PI Lab tour and Core Labs tour	14:00-17:00	
Nazek Elatab Lab tour by Galo Torres, Sea Side, L2, Building 3 (14:00-14:20)		
		Xiaohang Li Lab tour by Saravanan Yuvaraja, Desert Side, L2, Building 3 (14:20-14:40)
Bandgap Break at R2255 Desert Side, L2, Building 3 (14:40-15:00)		
		Discussion with Prof. Yating Wan at R2255 Desert Side, L2, Building 3 (15:00-15:40)
Visualization Core Lab Tour, Sea Side L2, Building 1 (15:45-16:00)		
Imaging and Characterization Core Lab Tour, L0, Building 3 (16:00-16:30)		
Nanofabrication Core Lab Tour, L0, Building 3 (16:30-17:00)		Nanotabrication Core Lab Tour, L0, Building 3 (16:30-17:00)
	17.10	
	17:10	Jeddah Tour and Guest Departure
THE END	17:10	Jeddah Tour and Guest Departure Taxi pickup location: Bus Stop, Building 16